IGBT缓冲吸收电容

Snubber Capacitor For IGBT





特点 / Introduction



●迈拉胶带封装,阻燃环氧树脂注塑;

Mylar tape, Sealed with epoxy resin;

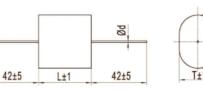
●镀锡铜线引出,方便安装;

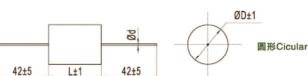
Tin plated copper wire lead, convenient installation;

●无感式结构,ESL低、ESR小,高脉冲电流,高DV/DT承 受能力;耐压高,损耗小,温升低,寿命长等特点。

Non inductive structure, ESL low, ESR small, high pulse current, high DV/DT bearing capacity, high pressure, low loss, low temperature rise, long life and so on.

外形图 / Outline Drawing





土

扁形Scetor

技术参数 / Technical Data

GB/T 17702、IEC61071
40/85/21
630V.DC~4000V.DC
0.0068 μ F~10 μ F
±5%(J)、±10%(K)
1.5Un(VDC)/60S
≥5000S(100VDC,60S at 20°C)

常用规格 / Dimension



Cn (µF)	Dimension(mm)			Φ.4	DV/DT	1-1-(1)	ESR	ESL	Irms(A)
	L	Т	н	Фф	(V/ µ S)	lpk(A)	(mΩ)	(nH)	@40°C
Un 630	V.DC	Us 945	V Ur40	00V.AC					
0.33	32	12	20	1.2	200	66	13	15	10
0.47	32	14.5	22.5	1.2	220	103	11	15	10
0.68	32	18	26	1.2	180	66	10	15	10
1.5	37	13.5	21.5	1.2	150	225	7	18	10
6.8	57	34	46.5	1.2	180	1224	3.5	25	15
Un 120	OV.DC	Us 180	ov Ur	550V.A0	0				
0.15	32	10	17.5	1.2	1200	180	18	15	10
0.47	32	17.5	30	1.2	1200	564	10	15	10
0.68	32	21.5	34	1.2	1100	748	8	15	12
1.5	44	26.5	39	1.2	950	1425	5	20	14
4.7	57	38	53.5	1.2	420	1974	3	25	20
Un 170	OV.DC	Us 255	ov Ur	600V.A0	0				
0.1	32	9.5	17.5	1.2	1300	130	18	15	10
0.33	32	18.5	26.5	1.2	1200	396	12	15	12
0.47	44	16	24	1.2	1000	470	9	20	13
0.68	44	20	28	1.2	1000	680	8	20	14
1.5	57	24	32	1.2	750	1125	5	25	15
Un 2000V.DC		Us 300	ov Ur	700V.A0	9				
0.068	32	9	17	1.2	1500	102	25	15	10
0.33	37	20	28	1.2	1250	413	12	15	12
0.68	44	24	36.5	1.2	1000	680	8	20	15
1	57	23.5	36	1.2	950	950	6	25	16
2	57	33	48.5	1.2	750	1500	4.2	25	18
Un 300	OV.DC	Us 450	ov Ur	750V.A0					
0.047	44	13.5	21.5	1.2	2000	94	22	20	10
0.068	44	17	25	1.2	1800	123	20	20	12
0.1	44	20.5	28.5	1.2	1500	150	18	20	14
0.15	44	26	28.5	1.2	1350	203	16	22	15
0.22	44	29	41.5	1.2	1200	264	15	22	16

GTO缓冲吸收电容

Buffer Absorption Capacity For GTO





MKPS-TC Series

应 用 / Application

- ●GTO缓冲吸收: GTO Snubber
- 广泛应用于电力电子设备中开 关器件关断时的尖峰电压, 尖峰电流

Widely used in power electronic equipment when the peak voltage, peak current absorption 典型应用电路 / Typical Circuit



Snubber Capacitors(C3)

特点 / Introduction

●迈拉胶带封装,阻燃环氧树脂注塑;

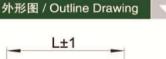
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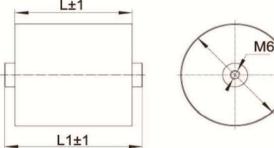
●镀锡铜线引出,方便安装;

Tin plated copper wire lead, convenient installation;

●无感式结构, ESL低、ESR小, 高脉冲电流, 高DV/DT承 受能力; 耐压高, 损耗小, 温升低, 寿命长等特点。

Non inductive structure, ESL low, ESR small, high pulse current, high DV/DT bearing capacity, high pressure, low loss, low temperature rise, long life and so on.

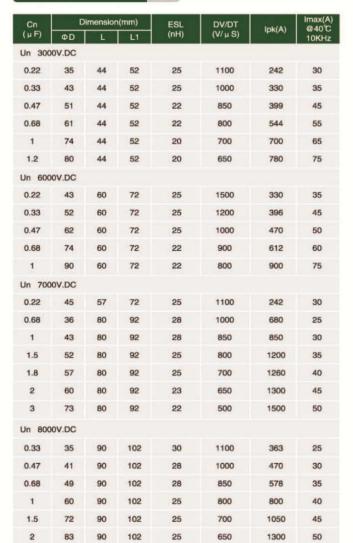




技术参数 / Technical Data

GB/T 17702、IEC61071
40/85/21
3000V.DC~20000V.DC
0.068 µ F~3 µ F
±5%(J)、±10%(K)
1.5Un(VDC)/60S
≥5000S(100VDC,60S at 20°C)

常用规格 / Dimension



ØD±2

2 Sunpper

IGBT缓冲吸收电容

Snubber Capacitor For IGBT





MKPS-P

Series

应用 / Application

- ●IGBT缓冲吸收; IGBT Snubber;
- ●广泛应用于电力电子设备中开关 器件关断时的尖峰电压,尖峰电流吸收 保护。

Widely used in power electronic equipment when the peak voltage, peak current absorption protection.



Snubber Capacitors(C3)

特点 / Introduction



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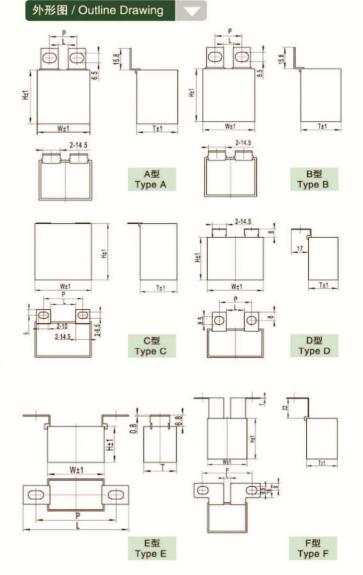
技术参数 / Technical Data



执行标准 Implemented Standard	GB/T 17702、IEC61071
气候等级 Climatic Category	40/85/21
额定电压 (Un)Rated Voltage	630V.DC~4000V.DC
容量范围 (Cn)Capacitance Range	0.0068 μ F~10 μ F
容量偏差 Capacitance Tolerance	±5%(J), ±10% (K)
耐电压 Withstand Voltage	
极间 Between Terminals	1.5Un(VDC)/60S
绝缘电阻 Insulation Resisitance	≥5000S(100VDC,60S at 20°C)

述 Type Description

项 目	W	L	P	Output
	42.5	10.5	22 ~ 29	M6
Type A	57.5	10.5	22 - 29	M6
	57.5	25.5	37 ~ 44	M6
Туре В	42.5	10.5	24 - 26	M8
	42.5	8	21 ~ 23	M8
	57.5	10.5	24~26	M8
	57.5	24	37 ~ 39	M8
Type C	42.5	10.5	22 - 29	M6
	57.5	10.5	22 - 29	M6
	57.5	25.5	37 - 44	M6
	42.5	10.5	24 - 26	M8
	42.5	8.5	22 - 24	M8
Type D	57.5	10.5	24 ~ 26	M8
	57.5	23.5	37 ~ 39	M8
Type E	42.5	80.5	60.5 - 64.5	M6
ype E	57.5	95.5	75.5 ~ 79.5	M6
Type F	57.5	21	51.5 ~ 62.5	M6



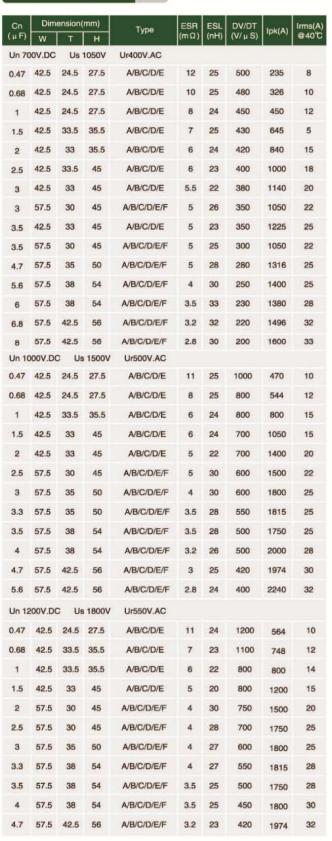
IGBT缓冲吸收电容

Snubber Capacitor For IGBT



MKPS-P Series

常用规格 / Dimension



Cn	Dim	ension((mm)	Туре	ESR (mΩ)	ESL (nH)	DV/DT (V/μS)	lpk(A)	Irms(A) @40℃
	700V.D	- 25	2250V	Ur575V.AC					
0.33	42.5	24.5	27.5	A/B/C/D/E	12	25	1300	429	9
0.47	42.5	33.5	35.5	A/B/C/D/E	10	24	1300	611	10
0.68	42.5	33.5	35.5	A/B/C/D/E	8	23	1300	884	12
1	42.5	33	45	A/B/C/D/E	7	22	1200	1200	15
1.5	42.5	33	45	A/B/C/D/E	6	22	1200	1800	18
1.5	57.5	30	45	A/B/C/D/E/F	5	31	1200	1800	20
2	57.5	30	45	A/B/C/D/E/F	5	30	1100	2200	22
2.5	57.5	30	50	A/B/C/D/E/F	4	28	1100	2750	25
3	57.5	38	54	A/B/C/D/E/F	4	27	700	2100	25
3.3	57.5	38	54	A/B/C/D/E/F	3.8	26	600	1980	28
3.5	57.5	42.5	56	A/B/C/D/E/F	3.5	25	500	1750	30
4	57.5	42.5	56	A/B/C/D/E/F	3.2	25	450	1800	32
Un 20	000V.D	C Us	3000V	Ur700V.AC					
0.22	42.5	24.5	27.5	A/B/C/D/E	15	25	1500	330	10
0.33	42.5	33.5	35.5	A/B/C/D/E	12	24	1500	495	12
0.47	42.5	33.5	35.5	A/B/C/D/E	11	23	1400	658	15
0.68	42.5	33	45	A/B/C/D/E	8	22	1200	816	18
0.68	57.5	30	45	A/B/C/D/E/F	7	30	1100	748	20
0.82	42.5	33	45	A/B/C/D/E	7	28	1200	984	22
1	57.5	30	45	A/B/C/D/E/F	6	28	1100	1100	25
1.5	57.5	35	50	A/B/C/D/E/F	5	25	1000	1500	28
2	57.5	38	54	A/B/C/D/E/F	5	24	800	1600	28
2.2	57.5	42.5	56	A/B/C/D/E/F	4	23	700	1540	32
Un 30	000V.D	C Us	4500V	Ur750V.AC					
0.15	42.5	33	45	A/B/C/D/E	18	28	2500	375	25
0.22	42.5	33	45	A/B/C/D/E	15	27	2200	484	28
0.22	57.5	35	50	A/B/C/D/E/F	15	25	2000	330	20
0.33	57.5	35	50	A/B/C/D/E/F	12	24	1800	495	20
0.47	57.5	38	54	A/B/C/D/E/F	11	23	1600	752	22
0.68	57.5	42.5	56	A/B/C/D/E/F	8	22	1500	1020	28